

PROCESS FOR FABRICATING A SHORT-GATE-LENGTH MOS  
TRANSISTOR AND INTEGRATED CIRCUIT COMPRISING SUCH A  
TRANSISTOR

Abstract of the Disclosure

A process for fabricating an integrated circuit includes forming a gate on a crystalline silicon substrate, and amorphizing a region of the substrate to obtain an amorphous silicon region. Dopant is implanted in a subregion lying substantially within the amorphous silicon region of the substrate to form drain and source extensions. A source and drain are then formed at a low temperature.